

BUK763R6-40C

N-channel TrenchMOS standard level FET Rev. 04 — 16 June 2010

Product data sheet

Product profile

1.1 General description

Standard level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Avalanche robust

- Suitable for standard level gate drive
- Suitable for thermally demanding environment up to 175°C rating

1.3 Applications

- 12V Motor, lamp and solenoid loads
- High performance automotive power systems
- High performance Pulse Width Modulation (PWM) applications



1.4 Quick reference data

Table 1. Quick reference data

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Parameter	Conditions		Min	Тур	мах	Unit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	40	V
drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	100	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	203	W
racteristics						
drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>		-	3	3.6	mΩ
ruggedness						
non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	292	mJ
haracteristics						
gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 32 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 14; see Figure 13		-	35	-	nC
	voltage drain current total power dissipation racteristics drain-source on-state resistance ruggedness non-repetitive drain-source avalanche energy	drain-source voltage $T_{j} \geq 25 \text{ °C}; T_{j} \leq 175 \text{ °C}$ $voltage$ $drain current$ $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ $see \underline{Figure 1}; see \underline{Figure 3}$ $total power \\ dissipation$ $racteristics$ $drain-source \\ on-state \\ resistance$ $v_{GS} = 10 \text{ V}; I_{D} = 25 \text{ A};$ $T_{j} = 25 \text{ °C};$ $resistance$ $v_{GS} = 10 \text{ V}; I_{D} = 25 \text{ A};$ $T_{j} = 25 \text{ °C};$ $see \underline{Figure 11}; see \underline{Figure 12}$ $ruggedness$ $non-repetitive \\ drain-source \\ avalanche energy$ $I_{D} = 100 \text{ A}; V_{sup} \leq 40 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; unclamped$ $ruggedness$ $v_{GS} = 10 \text{ V}; I_{D} = 25 \text{ A};$ $v_{DS} = 32 \text{ V}; T_{j} = 25 \text{ °C};$	drain-source voltage $ T_{j} \geq 25 \text{ °C}; T_{j} \leq 175 \text{ °C} $ voltage $ T_{j} \geq 25 \text{ °C}; T_{j} \leq 175 \text{ °C} $ drain current $ V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; $ see Figure 3 $ T_{mb} = 25 \text{ °C}; \text{ see Figure 2} $ total power dissipation $ T_{mb} = 25 \text{ °C}; \text{ see Figure 2} $ drain-source $ T_{mb} = 25 \text{ °C}; \text{ see Figure 2} $ drain-source $ T_{j} = 25 \text{ °C}; \text{ see Figure 12} $ registance $ T_{j} = 25 \text{ °C}; \text{ see Figure 12} $ ruggedness $ T_{j} = 25 \text{ °C}; \text{ see Figure 12} $ ruggedness $ T_{j} = 100 \text{ A}; V_{sup} \leq 40 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped characteristics} $ gate-drain charge $ V_{GS} = 10 \text{ V}; I_{D} = 25 \text{ A}; \text{ V}_{DS} = 32 \text{ V}; T_{j} = 25 \text{ °C}; $	drain-source voltage $T_{j} \geq 25 ^{\circ}\text{C}; T_{j} \leq 175 ^{\circ}\text{C} \qquad -$ voltage $\text{drain current} \qquad V_{GS} = 10 \text{V}; T_{mb} = 25 ^{\circ}\text{C}; \qquad \boxed{11} -$ see $ \frac{\text{Figure 1}}{\text{see Figure 3}}; \text{see Figure 2} \qquad -$ total power dissipation $\text{drain-source} \qquad V_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2} \qquad -$ drain-source on-state $T_{j} = 25 ^{\circ}\text{C}; \text{see Figure 12} \qquad -$ ruggedness $\text{non-repetitive} \qquad I_{D} = 100 \text{A}; V_{sup} \leq 40 \text{V}; -$ drain-source avalanche energy $\text{R}_{GS} = 50 \Omega; V_{GS} = 10 \text{V}; -$ drain-source avalanche energy $\text{R}_{GS} = 50 \Omega; V_{GS} = 10 \text{V}; -$ drain-source avalanche energy $\text{R}_{GS} = 50 \Omega; V_{GS} = 10 \text{V}; -$ drain-source avalanche energy $\text{R}_{GS} = 50 \Omega; V_{GS} = 10 \text{V}; -$ drain-source avalanche energy $\text{R}_{GS} = 50 \Omega; V_{GS} = 10 \text{V}; V_{GS} = 10 \text{V}; V_{GS} = 10 \text{V}; V_{GS} = 10 \text{V}; V_{GS} = 32 \text{V}; T_{j} = 25 ^{\circ}\text{C}; -$	drain-source voltage $T_{j} \geq 25 ^{\circ}\text{C}; T_{j} \leq 175 ^{\circ}\text{C} \qquad - \qquad $	drain-source voltage $T_{j} \geq 25 ^{\circ}\text{C}; T_{j} \leq 175 ^{\circ}\text{C} \qquad - \qquad 40$ drain current $V_{GS} = 10 \text{V}; T_{mb} = 25 ^{\circ}\text{C}; \qquad 111 \qquad - \qquad 100$ total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2} \qquad - \qquad - \qquad 203$ drain-source drain-source on-state $T_{j} = 25 ^{\circ}\text{C}; \text{see Figure 12}$ drain-source see Figure 11; see Figure 12 $T_{j} = 25 ^{\circ}\text{C}; \text{see Figure 12}$ drain-source $T_{j} = 100 \text{A}; V_{sup} \leq 40 \text{V}; - \qquad 292 \text{C}; \text{con-repetitive drain-source}$ avalanche energy $T_{j(init)} = 25 ^{\circ}\text{C}; \text{unclamped}$ drain-charge $T_{j} = 100 \text{A}; V_{sup} \leq 40 \text{V}; - \qquad 292 \text{C}; \text{unclamped}$

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		D
3	S	source		g (EX)
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK763R6-40C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

BUK763R6-40C

4. Limiting values

Table 4. Limiting values

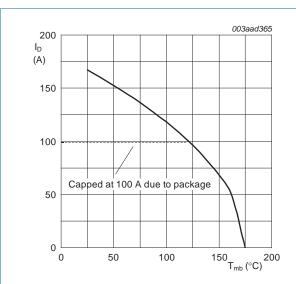
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	40	V
V_{GS}	gate-source voltage		<u>[1]</u>	-20	-	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	-	167	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	[3]	-	-	100	Α
		T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[3]	-	-	100	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3		-	-	668	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	203	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	diode						
I _S	source current	$T_{mb} = 25 ^{\circ}C$	[3]	-	-	100	Α
			[2]	-	-	167	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	668	Α
Avalanche rug	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 100 \text{ A; } V_{sup} \leq 40 \text{ V; } R_{GS} = 50 \Omega; \\ V_{GS} &= 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } unclamped \end{split}$		-	-	292	mJ

^{[1] -20}V accumulated duration not to exceed 168 hrs.

^[2] Current is limited by power dissipation chip rating.

^[3] Continuous current is limited by package.



 $V_{GS} \ge 10 V(1)$ Capped at 100A due to package

Fig 1. Continuous drain current as a function of mounting base temperature

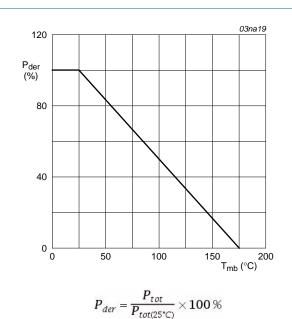
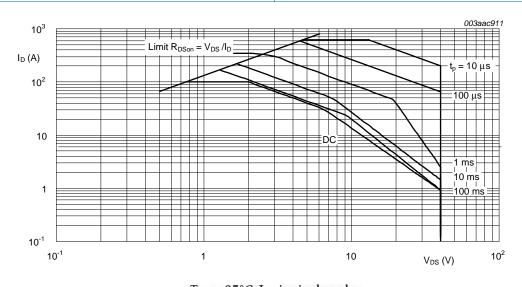


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.74	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed circuit board; minimum footprint; SOT404 package	-	-	50	K/W

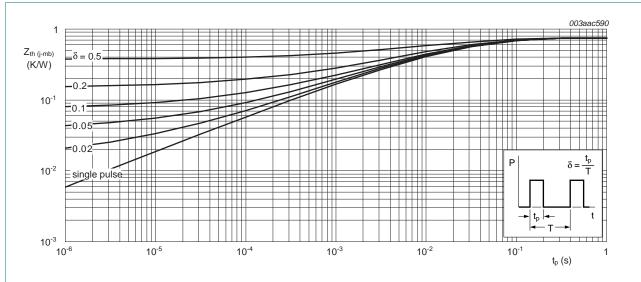


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	40	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 20 V; T _j = 25 °C	-	2	100	nA
		V _{DS} = 0 V; V _{GS} = -20 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 11	-	-	7.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11; see Figure 12	-	3	3.6	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	97	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	21	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 ^{\circ}\text{C}; \text{see } \frac{\text{Figure } 14}{\text{Figure } 13}$	-	35	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	4391	5708	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	800	1040	pF
C _{rss}	reverse transfer capacitance		-	535	696	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	40	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	95	-	ns
t _{d(off)}	turn-off delay time		-	129	-	ns
t _f	fall time		-	92	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_i = 25$ °C	-	4.5	-	nΗ
		from contact screw on mounting base to centre of die; T _j = 25 °C	-	3.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; T _i = 25 °C	-	7.5	-	nΗ
Source-di	rain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 16	-	0.83	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	44	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	57	-	nC

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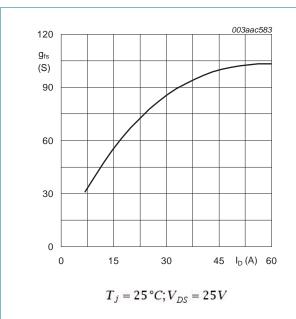
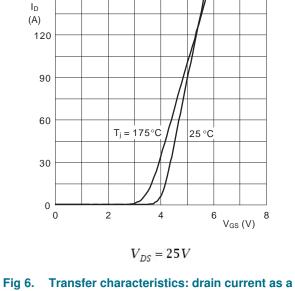


Fig 5. Forward transconductance as a function of drain current; typical values



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Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

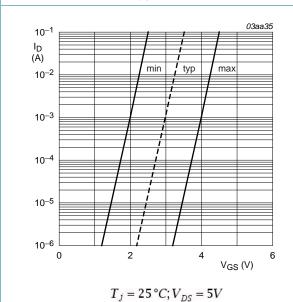
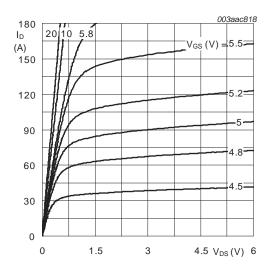
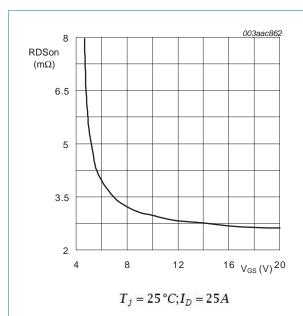


Fig 7. Sub-threshold drain current as a function of gate-source voltage

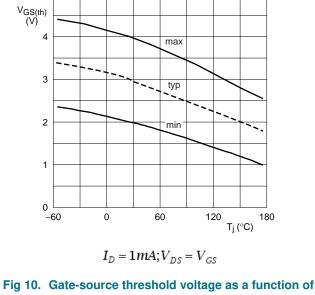


 $T_j = 25 \,^{\circ}C; t_p = 300 \mu s$

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



Drain-source on-state resistance as a function Fig 9. of gate voltage; typical values



5

junction temperature

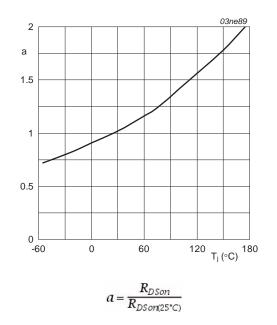


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

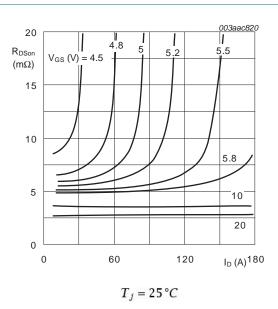
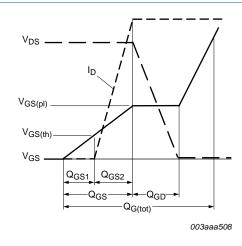


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

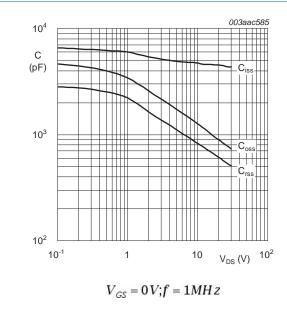
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 $T_j = 25 \,^{\circ}C$

Fig 13. Gate charge waveform definitions

Fig 14. Gate-source voltage as a function of gate charge; typical values



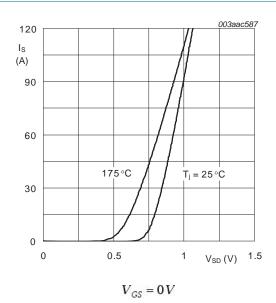


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

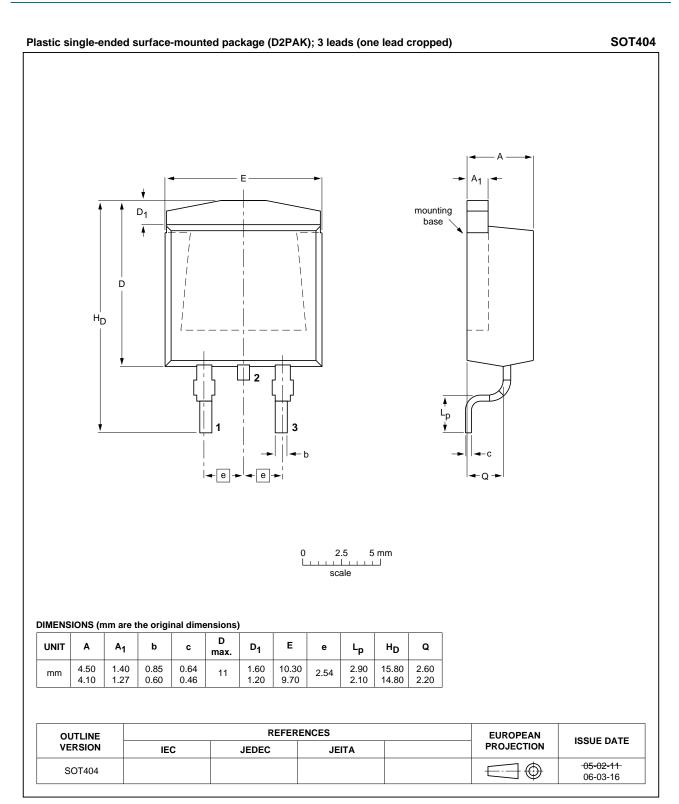


Fig 17. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK763R6-40C v.4	20100616	Product data sheet	-	BUK763R6-40C v.3
Modifications:	 Various cha 	anges to content.		
BUK763R6-40C v.3	20100602	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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11. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data2
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13